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FSD156MRBN Green-Mode Fairchild Power Switch (FPS™)

Features

- Advanced Soft Burst-Mode Operation for Low Standby Power and Low Audible Noise
- Random Frequency Fluctuation (RFF) for Low EMI
- Pulse-by-Pulse Current Limit
- Various Protection Functions: Overload Protection (OLP), Over-Voltage Protection (OVP), Abnormal Over-Current Protection (AOCP), Internal Thermal Shutdown (TSD) with Hysteresis, Output-Short Protection (OSP), and Under-Voltage Lockout (UVLO) with Hysteresis
- Low Operating Current (0.4mA) in Burst Mode
- Internal Startup Circuit
- Internal High-Voltage SenseFET: 650V
- Built-in Soft-Start: 15ms
- Auto-Restart Mode

Applications

 Power Supply for LCD Monitor, STB, and DVD Combination

Description

The FSD156MRBN is an integrated Pulse Width Modulation (PWM) controller and SenseFET specifically designed for offline Switch-Mode Power Supplies (SMPS) with minimal external components. The PWM controller includes an integrated fixed-frequency oscillator, Under-Voltage Lockout (UVLO), Leading-Edge Blanking (LEB), optimized gate driver, internal soft-start, temperature-compensated precise current sources for loop compensation, and self-protection circuitry. Compared with a discrete MOSFET and PWM controller solution, the FSD series can reduce total cost, weight; component count. and size. simultaneously increasing efficiency, productivity, and system reliability. This device provides a basic platform suited for cost-effective design of a flyback converter.

Ordering Information

					Output Power Table ⁽²⁾					
Part Number	Package	Operating Junction Temperature	Current Limit	/B/I \(\)	230V _{AC} ±15% ⁽³⁾		85-265V _{AC}		Replaces	
r art Number					Adapter ⁽⁴⁾	Open Frame ⁽⁵⁾	Adapter ⁽⁴⁾	Open Frame ⁽⁵⁾	Device	
FSD156MRBN	8-DIP	−40°C ~ +125°C	1.60A	2.3Ω	26W	40W	20W	30W	FSFM300N FSGM300	

Notes:

- Lead-free package per JEDEC J-STD-020B.
- 2. The junction temperature can limit the maximum output power.
- 3. 230V_{AC} or 100/115V_{AC} with voltage doubler.
- 4. Typical continuous power in a non-ventilated enclosed adapter measured at 50°C ambient temperature.
- 5. Maximum practical continuous power in an open-frame design at 50°C ambient temperature.

Application Circuit

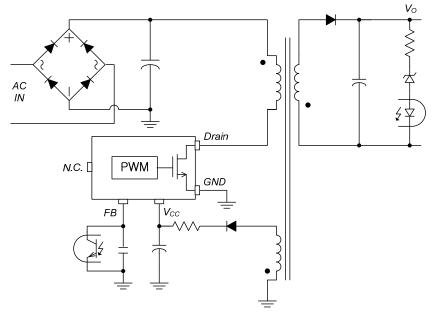


Figure 1. Typical Application Circuit

Internal Block Diagram

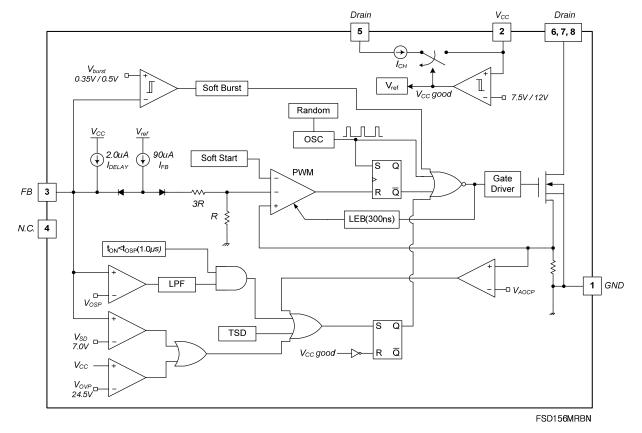


Figure 2. Internal Block Diagram

Pin Configuration

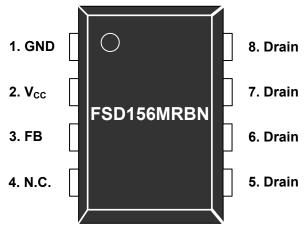


Figure 3. Pin Configuration (Top View)

Pin Definitions

Pin#	Name	Description
1	GND	Ground. This pin is the control ground and the SenseFET source.
2	V _{CC}	Power Supply . This pin is the positive supply input, which provides the internal operating current for both startup and steady-state operation.
3	FB	Feedback . This pin is internally connected to the inverting input of the PWM comparator. The collector of an opto-coupler is typically tied to this pin. For stable operation, a capacitor should be placed between this pin and GND. If the voltage of this pin reaches 7.0V, the overload protection triggers, which shuts down the FPS™.
4	NC	No Connection
5, 6, 7, 8	Drain	SenseFET Drain. High-voltage power SenseFET drain connection.

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol		Parameter		Min.	Max.	Unit
V _{DS}	Drain Pin Voltage				650	V
V _{CC}	V _{CC} Pin Voltage				26	V
V_{FB}	Feedback Pin Voltage			-0.3	10.0	V
I _{DM}	Drain Current Pulsed				4	А
	Continuous Switching Drain Current ⁽⁶⁾ T _C =25°C				1.9	А
I _{DS}	Continuous Switching	T _C =100°C			1.27	Α
E _{AS}	Single Pulsed Avalance	he Energy ⁽⁷⁾	<u>.</u>		190	mJ
P _D	Total Power Dissipatio	n (T _C =25°C) ⁽⁸⁾			1.5	W
_	Maximum Junction Te	mperature			150	°C
TJ	Operating Junction Te	-40	+125	°C		
T _{STG}	Storage Temperature		-55	+150	°C	
ECD	Electrostatic Human Body Model, JESD22-A114 Discharge Capability Charged Device Model, JESD22-C101				5	147
ESD					2	kV

Notes:

- 6. Repetitive peak switching current when the inductive load is assumed: Limited by maximum duty (D_{MAX}=0.73) and junction temperature (see Figure 4).
- 7. L=45mH, starting T_J=25°C.
- 8. Infinite cooling condition (refer to the SEMI G30-88).
- 9. Although this parameter guarantees IC operation, it does not guarantee all electrical characteristics.

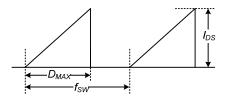


Figure 4. Repetitive Peak Switching Current

Thermal Impedance

T_A=25°C unless otherwise specified.

Symbol	Parameter	Value	Unit
θ_{JA}	Junction-to-Ambient Thermal Impedance ⁽¹⁰⁾	85	°C/W
Ψ_{JL}	Junction-to-Lead Thermal Impedance ⁽¹¹⁾	11	°C/W

Notes:

- 10. JEDEC recommended environment, JESD51-2, and test board, JESD51-10, with minimum land pattern.
- 11. Measured on the SOURCE pin #7, close to the plastic interface.

Electrical Characteristics

 $T_J = 25^{\circ}C$ unless otherwise specified.

Symbol	Parameter		Conditions	Min.	Тур.	Max.	Unit
SenseFET	Section		1				
BV _{DSS}	Drain-Source Breakdown Voltage		$V_{CC} = 0V, I_D = 250\mu A$	650			V
I _{DSS}	Zero-Gate-Voltage Drain Current		V _{DS} = 650V, T _A = 25°C			250	μΑ
R _{DS(ON)}	Drain-Source C	n-State Resistance	V _{GS} =10V, I _D =1A		1.8	2.2	Ω
C _{ISS}	Input Capacitar	nce ⁽¹²⁾	$V_{DS} = 25V, V_{GS} = 0V, f=1MHz$		515		pF
Coss	Output Capacita	ance ⁽¹²⁾	$V_{DS} = 25V, V_{GS} = 0V, f=1MHz$		75		pF
t _r	Rise Time		$V_{DS} = 325V$, $I_D = 4A$, $R_G = 25\Omega$		26		ns
t _f	Fall Time		$V_{DS} = 325V$, $I_D = 4A$, $R_G = 25\Omega$		25		ns
t _{d(on)}	Turn-On Delay		$V_{DS} = 325V$, $I_D = 4A$, $R_G = 25\Omega$		14		ns
$t_{d(off)}$	Turn-Off Delay		V_{DS} = 325V, I_D = 4A, R_G =25 Ω		32		ns
Control Sec	ction						
f _S	Switching Frequency	uency ⁽¹²⁾	V _{CC} = 14V, V _{FB} = 4V	61	67	73	kHz
Δf _S	Switching Frequency	uency Variation ⁽¹²⁾	-25°C < T _J < 125°C		±5	±10	%
D_MAX	Maximum Duty	Ratio	V _{CC} = 14V, V _{FB} = 4V	61	67	73	%
D _{MIN}	Minimum Duty	Ratio	V _{CC} = 14V, V _{FB} = 0V			0	%
I _{FB}	Feedback Sour	ce Current	V _{FB} = 0	65	90	115	μΑ
V _{START}	UVLO Threshold Voltage		V _{FB} = 0V, V _{CC} Sweep	11	12	13	V
V _{STOP}			After Turn-on, V _{FB} = 0V	7.0	7.5	8.0	V
t _{SS}	Internal Soft-St	art Time	V _{STR} = 40V, V _{CC} Sweep		15		ms
V_{RECOMM}	Recommended	V _{CC} Range		13		23	V
Burst-Mode	Section						
V_{BURH}				0.45	0.50	0.55	V
V_{BURL}	Burst-Mode Vol	tage	V _{CC} = 14V, V _{FB} Sweep	0.30	0.35	0.40	V
Hys					150		mV
Protection	Section						
I _{LIM}	Peak Drain Cur	rent Limit	di/dt = 300mA/μs	1.45	1.60	1.75	Α
V _{SD}	Shutdown Feed	lback Voltage	V _{CC} = 14V, V _{FB} Sweep	6.45	7.00	7.55	V
I _{DELAY}	Shutdown Dela	y Current	V _{CC} = 14V, V _{FB} = 4V	1.2	2.0	2.8	μΑ
t _{LEB}	Leading-Edge Blanking Time ^(12,14)				300		ns
V _{OVP}	Over-Voltage P	rotection	V _{CC} Sweep	23.0	24.5	26.0	V
t _{OSP}	Threshold Time		OSP Triggered when	0.7	1.0	1.3	μS
V _{OSP}	Output-Short Protection ⁽¹²⁾	Threshold V _{FB}	ton <tosp &="" vfb="">Vosp</tosp>	1.8	2.0	2.2	V
t _{OSP_FB}	V _{FB} Blanking Time		(Lasts Longer than t _{OSP_FB})	2.0	2.5	3.0	μS
TSD	T	_ (12)	Shutdown Temperature	125	135	145	°C
T _{HYS}	I hermal Shutdo	own Temperature ⁽¹²⁾	Hysteresis		60		°C

Continued on the following page...

Electrical Characteristics (Continued)

 T_J = 25°C unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit		
Total Devic	Total Device Section							
I _{OP}	Operating Supply Current, (Control Part in Burst Mode)	V _{CC} = 14V, V _{FB} = 0V	0.3	0.4	0.5	mA		
I _{OPS}	Operating Switching Current, (Control Part and SenseFET Part)	V _{CC} = 14V, V _{FB} = 2V	1.1	1.5	1.9	mA		
I _{START}	Start Current	V _{CC} =11V (Before V _{CC} Reaches V _{START})	85	120	155	μΑ		
I _{CH}	Startup Charging Current	$V_{CC} = V_{FB} = 0V$, $V_{STR} = 40V$	0.7	1.0	1.3	mA		
V_{STR}	Minimum V _{STR} Supply Voltage	$V_{CC} = V_{FB} = 0V$, V_{STR} Sweep		26		V		

Notes:

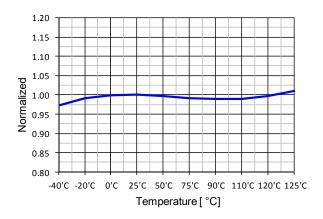
- 12. Although these parameters are guaranteed, they are not 100% tested in production.
- 13. Average value.
- 14. t_{LEB} includes gate turn-on time.

Comparison of FSGM300N and FSD156MRBN

Function	FSGM300N	FSD156MRBN	Advantages of FSD156MRBN
Operating Current	1.5mA	0.4mA	Very low standby power
Power Balance	Long t _{CLD}	Very Short t _{CLD}	The difference of input power between the low and high input voltage is quite small.

Typical Performance Characteristics

Characteristic graphs are normalized at T_A=25°C.



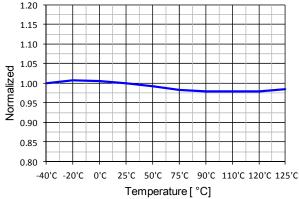
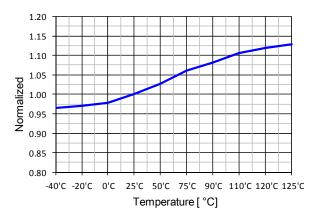


Figure 5. Operating Supply Current (IOP) vs. TA

Figure 6. Operating Switching Current (I_{OPS}) vs. T_A



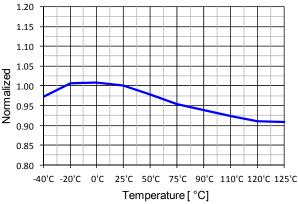
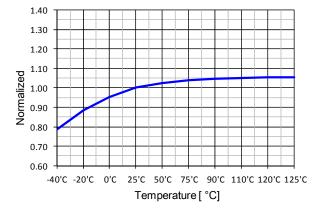


Figure 7. Startup Charging Current (I_{CH}) vs. T_A

Figure 8. Peak Drain Current Limit (I_{LIM}) vs. T_A



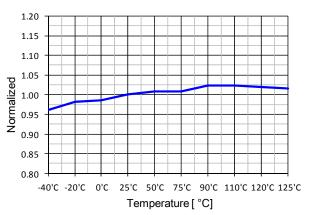
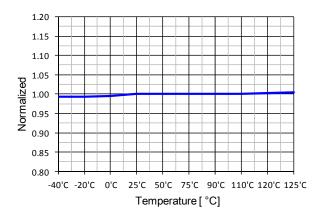


Figure 9. Feedback Source Current (IFB) vs. TA

Figure 10. Shutdown Delay Current (I_{DELAY}) vs. T_A

Typical Performance Characteristics

Characteristic graphs are normalized at T_A=25°C.



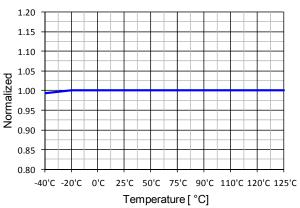
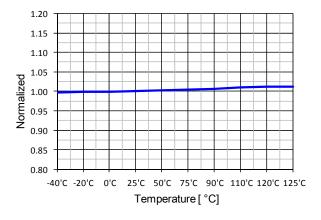


Figure 11. UVLO Threshold Voltage (V_{START}) vs. T_A

Figure 12. UVLO Threshold Voltage (V_{STOP}) vs. T_A



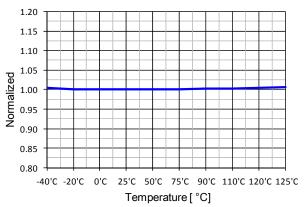


Figure 13. Shutdown Feedback Voltage (V_{SD}) vs. T_A

Figure 14. Over-Voltage Protection (V_{OVP}) vs. T_A

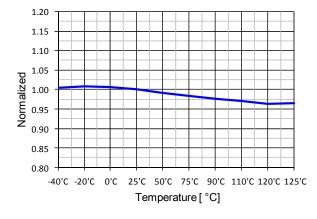


Figure 15. Switching Frequency (f_S) vs. T_A

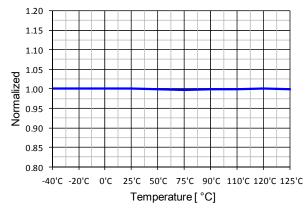


Figure 16. Maximum Duty Ratio (D_{MAX}) vs. T_A

Functional Description

1. Startup: At startup, an internal high-voltage current source supplies the internal bias and charges the external capacitor (C_{Vcc}) connected to the V_{CC} pin, as illustrated in Figure 17. When V_{CC} reaches 12V, the FSD156MRBN begins switching and the internal high-voltage current source is disabled. Normal switching operation continues and the power is supplied from the auxiliary transformer winding unless V_{CC} goes below the stop voltage of 7.5V.

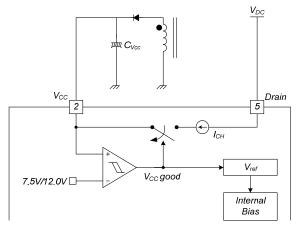


Figure 17. Startup Block

2. Soft-Start: The internal soft-start circuit increases PWM comparator inverting input voltage, together with the SenseFET current, slowly after startup. The typical soft-start time is 15ms. The pulse width to the power switching device is progressively increased to establish the correct working conditions for the transformers, inductors, and capacitors. The voltage on the output capacitors is progressively increased to smoothly establish the required output voltage. This helps prevent transformer saturation and reduces stress on the secondary diode during startup.

- **3. Feedback Control**: This device employs Current-Mode control, as shown in Figure 18. An opto-coupler (such as the FOD817) and shunt regulator (such as the KA431) are typically used to implement the feedback network. Comparing the feedback voltage with the voltage across the R_{SENSE} resistor makes it possible to control the switching duty cycle. When the reference pin voltage of the shunt regulator exceeds the internal reference voltage of 2.5V, the opto-coupler LED current increases, pulling down the feedback voltage and reducing drain current. This typically occurs when the input voltage is increased or the output load is decreased.
 - 3.1 Pulse-by-Pulse Current Limit: Because Current-Mode control is employed, the peak current through the SenseFET is limited by the inverting input of PWM comparator (V_{FB}^*), as shown in Figure 18. Assuming that the 90µA current source flows only through the internal resistor (3R + R =25k Ω), the cathode voltage of diode D2 is about 2.8V. Since D1 is blocked when the feedback voltage (V_{FB}) exceeds 2.8V, the maximum voltage of the cathode of D2 is clamped at this voltage. Therefore, the peak value of the current through the SenseFET is limited.
 - **3.2 Leading-Edge Blanking (LEB)**: At the instant the internal SenseFET is turned on, a high-current spike usually occurs through the SenseFET, caused by primary-side capacitance and secondary-side rectifier reverse recovery. Excessive voltage across the R_{SENSE} resistor leads to incorrect feedback operation in the Current-Mode PWM control. To counter this effect, the leading-edge blanking (LEB) circuit inhibits the PWM comparator for t_{LEB} (300ns) after the SenseFET is turned on.

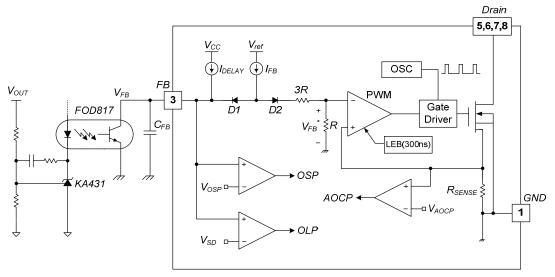


Figure 18. Pulse Width Modulation Circuit

4. Protection Circuits: The FSD156MRBN has several self-protective functions, such as Overload Protection (OLP), Abnormal Over-Current Protection (AOCP), Output-Short Protection (OSP), Over-Voltage Protection (OVP), and Thermal Shutdown (TSD). All the protections are implemented as auto-restart. Once the fault condition is detected, switching is terminated and the SenseFET remains off. This causes V_{CC} to fall. When V_{CC} falls to the Under-Voltage Lockout (UVLO) stop voltage of 7.5V, the protection is reset and the startup circuit charges the V_{CC} capacitor. When V_{CC} reaches the start voltage of 12.0V, the FSD156MRBN resumes normal operation. If the fault condition is not removed, the SenseFET remains off and V_{CC} drops to stop voltage again. In this manner, the auto-restart can alternately enable and disable the switching of the power SenseFET until the fault condition is eliminated. Because these protection circuits are fully integrated into the IC without external components, reliability is improved without increasing cost.

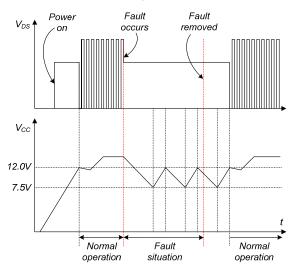


Figure 19. Auto-Restart Protection Waveforms

4.1 Overload Protection (OLP): Overload is defined as the load current exceeding its normal level due to an unexpected abnormal event. In this situation, the protection circuit should trigger to protect the SMPS. However, even when the SMPS is in normal operation, the overload protection circuit can be triggered during the load transition. To avoid this undesired operation, the overload protection circuit is designed to trigger only after a specified time to determine whether it is a transient situation or a true overload situation. Because of the pulse-by-pulse current limit capability, the maximum peak current through the SenseFET is limited and, therefore, the maximum input power is restricted with a given input voltage. If the output consumes more than this maximum power, the output voltage (Vout) decreases below the set voltage. This reduces the current through the opto-coupler LED, which also reduces the opto-coupler transistor current, increasing the feedback voltage (VFB). If VFB exceeds 2.5V, D1 is blocked and the 2.0µA current source starts to charge CFB slowly up. In this condition, VFB continues

increasing until it reaches 7.0V, when the switching operation is terminated, as shown in Figure 20. The delay for shutdown is the time required to charge C_{FB} from 2.5V to 7.0V with 2.0µA. A 25 \sim 50ms delay is typical for most applications. This protection is implemented in Auto-Restart Mode.

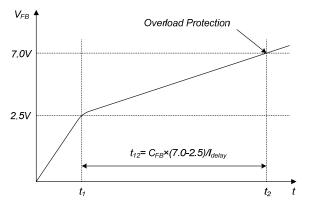


Figure 20. Overload Protection

4.2 Abnormal Over-Current Protection (AOCP): When the secondary rectifier diodes or the transformer pins are shorted, a steep current with extremely high di/dt can flow through the SenseFET during the minimum turn-on time. Even though the FSD156MRBN has overload protection, it is not enough to protect the FSD156MRBN in that abnormal case; due to the severe current stress imposed on the SenseFET until OLP is triggered. The internal AOCP circuit is shown in Figure 21. When the gate turn-on signal is applied to the power SenseFET, the AOCP block is enabled and monitors the current through the sensing resistor. The voltage across the resistor is compared with a preset AOCP level. If the sensing resistor voltage is greater than the AOCP level, the set signal is applied to the S-R latch, resulting in the shutdown of the SMPS.

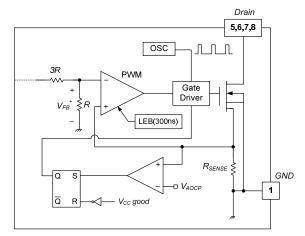


Figure 21. Abnormal Over-Current Protection

4.3. Output-Short Protection (OSP): If the output is shorted, steep current with extremely high di/dt can flow through the SenseFET during the minimum turnon time. Such a steep current brings high-voltage stress on the drain of the SenseFET when turned off. To protect the device from this abnormal condition, OSP is included. It is comprised of detecting V_{FB} and SenseFET turn-on time. When the V_{FB} is higher than 2.0V and the SenseFET turn-on time is lower than 1.0µs, this condition is recognized as an abnormal error and PWM switching shuts down until V_{CC} reaches V_{START} again. An abnormal condition output short is shown in Figure 22.

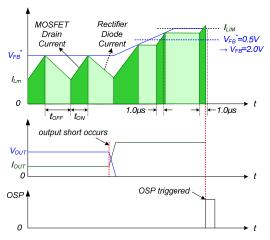


Figure 22. Output-Short Protection

- 4.4 Over-Voltage Protection (OVP): If secondary-side feedback circuit malfunctions or a solder defect causes an opening in the feedback path, the current through the opto-coupler transistor becomes almost zero. Then V_{FB} climbs up in a similar manner to the overload situation, forcing the preset maximum current to be supplied to the SMPS until the overload protection is triggered. Because more energy than required is provided to the output, the output voltage may exceed the rated voltage before the overload protection is triggered, resulting in the breakdown of the devices in the secondary side. To prevent this situation, an OVP circuit is employed. In general, the V_{CC} is proportional to the output voltage and the FSD156MRBN uses V_{CC} instead of directly monitoring the output voltage. If V_{CC} exceeds 24.5V, an OVP circuit is triggered, resulting in the termination of the switching operation. To avoid undesired activation of OVP during normal operation, V_{CC} should be designed to be below 24.5V.
- **4.5 Thermal Shutdown (TSD)**: The SenseFET and the control IC on a die in one package makes it easier for the control IC to detect the over temperature of the SenseFET. If the temperature exceeds ~135°C, the thermal shutdown is triggered and stops operation. The FSD156MRBN operates in Auto-Restart Mode until the temperature decreases to around 75°C, when normal operation resumes.

5. Soft Burst-Mode Operation: To minimize power dissipation in Standby Mode, the FSD156MRBN enters Burst-Mode operation. As the load decreases, the feedback voltage decreases. As shown in Figure 23, the device automatically enters Burst Mode when the feedback voltage drops below V_{BURL} (350mV). At this point, switching stops and the output voltages start to drop at a rate dependent on standby current load. This causes the feedback voltage to rise. Once it passes V_{BURH} (500mV), switching resumes. The feedback voltage then falls and the process repeats. Burst Mode alternately enables and disables SenseFET switching, reducing switching loss in Standby Mode.

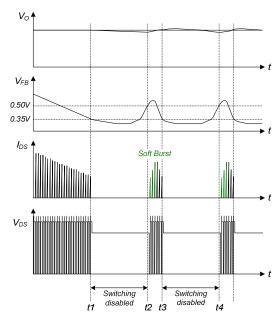


Figure 23. Figure 23. Burst-Mode Operation

6. Random Frequency Fluctuation (RFF): Fluctuating switching frequency of an SMPS can reduce EMI by spreading the energy over a wide frequency range. The amount of EMI reduction is directly related to the switching frequency variation, which is limited internally. The switching frequency is determined randomly by external feedback voltage and internal free-running oscillator at every switching instant. RFF effectively scatters EMI noise around typical switching frequency (67kHz) and can reduce the cost of the input filter included to meet the EMI requirements (e.g. EN55022).

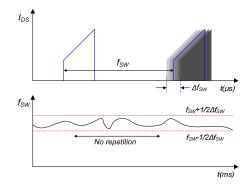


Figure 24. Random Frequency Fluctuation

Typical Application Circuit

Application	Input Voltage	Rated Output	Rated Power
LCD Monitor Power Supply	85 ~ 265V _{AC}	5.0V(2A) 14.0V(1.3A)	28.2W

Key Design Notes

- 1. The delay for overload protection is designed to be about 30ms with C105 (8.2nF). OLP time between 39ms (12nF) and 46ms (15nF) is recommended.
- 2. The SMD-type capacitor (C106) must be placed as close as possible to the V_{CC} pin to avoid malfunction by abrupt pulsating noises and to improve ESD and surge immunity. Capacitance between 100nF and 220nF is recommended.

Schematic

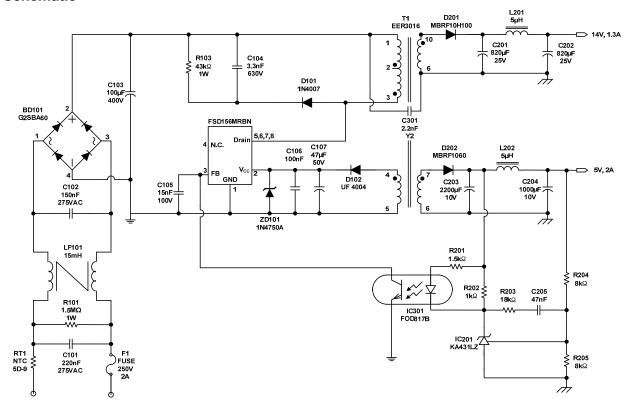


Figure 25. Schematic

Transformer

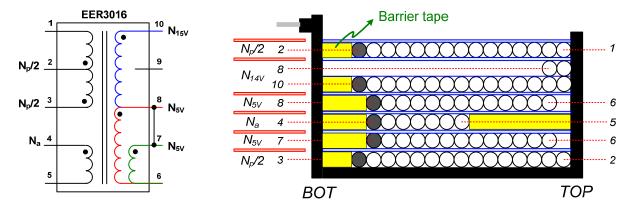


Figure 26. Schematic of Transformer

Winding Specification

	Dim/C F)	Wire Turn	T	Minding Mathed	Barrier Tape				
	Pin(S → F)	vvire	Turns	Winding Method	ТОР	вот	Ts		
N _p /2	3 → 2	0.25φ×1	22	Solenoid Winding	-	2.0mm	1		
Insulation: Polyest	Insulation: Polyester Tape t = 0.025mm, 2 Layers								
N _{5V}	7 → 6	0.4φ×2 (TIW)	3	Solenoid Winding	-	3.0mm	1		
Insulation: Polyest	Insulation: Polyester Tape t = 0.025mm, 2 Layers								
Na	4 → 5	0.2φ×1	8	Solenoid Winding	4.0mm	3.0mm	1		
Insulation: Polyest	er Tape t = 0.025n	nm, 2 Layers							
N _{5V}	8 → 6	0.4φ×2 (TIW)	3	Solenoid Winding	-	3.0mm	1		
Insulation: Polyest	er Tape t = 0.025n	nm, 2 Layers							
N _{14V}	10 → 8	0.4φ×2 (TIW)	5	Solenoid Winding		2.0mm	1		
Insulation: Polyester Tape t = 0.025mm, 2 Layers									
N _p /2	2 → 1	0.25φ×1	22	Solenoid Winding	-	2.0mm	1		
Insulation: Polyester Tape t = 0.025mm, 2 Layers									

Electrical Characteristics

	Pin	Specification	Remark
Inductance	1-3	826μH ±6%	67kHz, 1V
Leakage	1-3	15μH Maximum	Short all other pins

Core & Bobbin

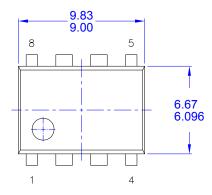
Core: EER3016 (Ae=109.7mm²)

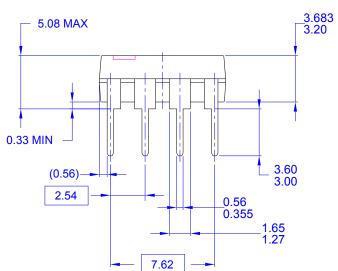
■ Bobbin: EER3016

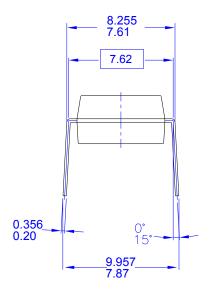
Bill of Materials

Part #	Value	Note	Part #	Value	Note	
	Fuse		Capacitor			
F101	250V 2A		C101	220nF/275V	Box (Pilkor)	
	NTC		C102	150nF/275V	Box (Pilkor)	
NTC101	5D-9	DSC	C103	100μF/400V	Electrolytic (SamYoung)	
	Resistor		C104	3.3nF/630V	Film (Sehwa)	
R101	1.5MΩ, J	1W	C105	15nF/100V	Film (Sehwa)	
R103	43kΩ, J	1W	C106	100nF	SMD (2012)	
R201	1.5kΩ, F	1/4W, 1%	C107	47μF/50V	Electrolytic (SamYoung)	
R202	1.0kΩ, F	1/4W, 1%	C201	820μF/25V	Electrolytic (SamYoung)	
R203	18kΩ, F	1/4W, 1%	C202	820μF/25V	Electrolytic (SamYoung)	
R204	8kΩ, F	1/4W, 1%	C203	2200μF/10V	Electrolytic (SamYoung)	
R205	8kΩ, F	1/4W, 1%	C204	1000μF/16V	Electrolytic (SamYoung)	
			C205	47nF/100V	Film (Sehwa)	
			C301	2.2nF/Y2	Y-cap (Samhwa)	
	IC		Inductor			
FPS	FSD156MRBN	Fairchild	LF101	20mH	Line filter 0.5Ø	
IC201	KA431LZ	Fairchild	L201	5μΗ	5A Rating	
IC301	FOD817B	Fairchild	L202	5μΗ	5A Rating	
	Diode		Transformer			
D101	1N4007	Vishay	T101	826uH		
D102	UF4007	Vishay				
ZD101	1N4750	Vishay				
D201	MBRF10H100	Fairchild				
D202	MBRF1060	Fairchild				
BD101	G2SBA60	Vishay				

Package Dimensions







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Figure 27. 8-Lead, MDIP, JEDEC MS-001, .300" Wide

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